

# MMBD7000LT1

Preferred Device

## Dual Switching Diode

### Features

- Pb-Free Packages are Available

### MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	100	Vdc
Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

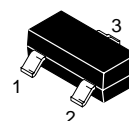
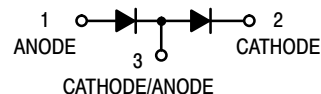
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



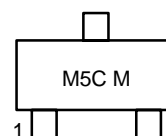
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236AB)  
CASE 318-08  
STYLE 8

### MARKING DIAGRAM



M5C = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping†
MMBD7000LT1	SOT-23	3000 Tape & Reel
MMBD7000LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBD7000LT3	SOT-23	10,000 Tape & Reel
MMBD7000LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

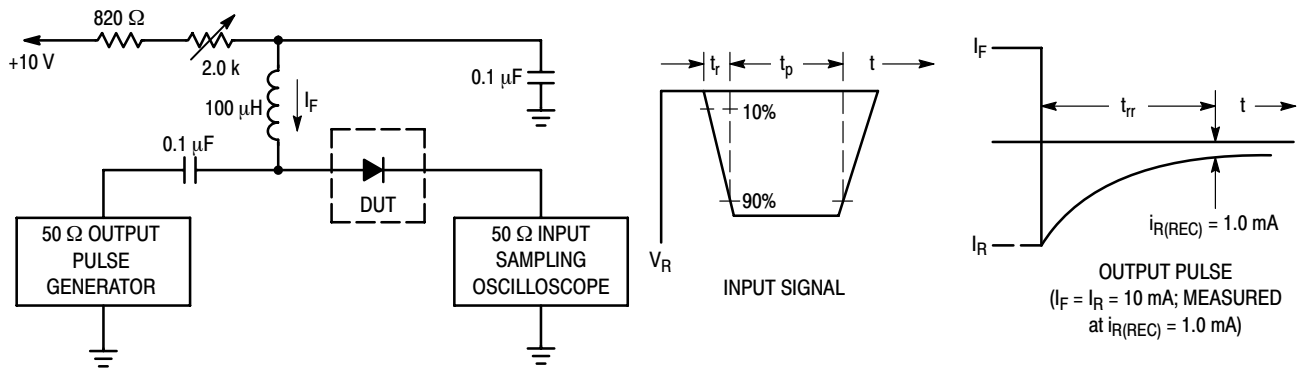
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MMBD7000LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Reverse Breakdown Voltage ( $I_{BR} = 100 \mu\text{A}$ )	$V_{(BR)}$	100	-	Vdc
Reverse Voltage Leakage Current ( $V_R = 50 \text{ Vdc}$ ) ( $V_R = 100 \text{ Vdc}$ ) ( $V_R = 50 \text{ Vdc}, 125^\circ\text{C}$ )	$I_R$ $I_{R2}$ $I_{R3}$	- - -	1.0 3.0 100	$\mu\text{A}$
Forward Voltage ( $I_F = 1.0 \text{ mA}$ ) ( $I_F = 10 \text{ mA}$ ) ( $I_F = 100 \text{ mA}$ )	$V_F$	0.55 0.67 0.75	0.7 0.82 1.1	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mA}$ ) (Figure 1)	$t_{rr}$	-	4.0	ns
Capacitance ( $V_R = 0 \text{ V}$ )	C	-	1.5	pF



- Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

# MMBD7000LT1

## CURVES APPLICABLE TO EACH DIODE

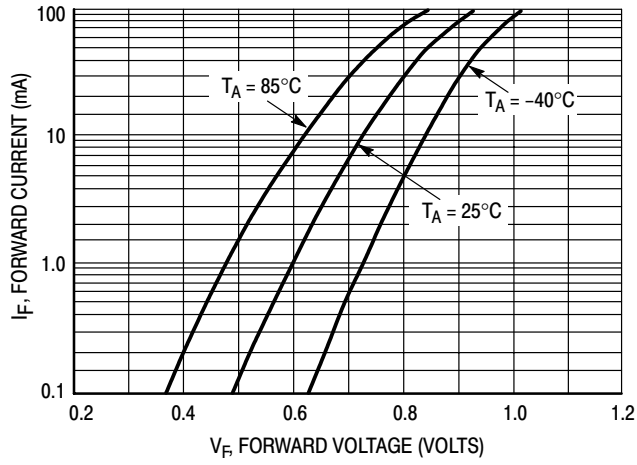


Figure 2. Forward Voltage

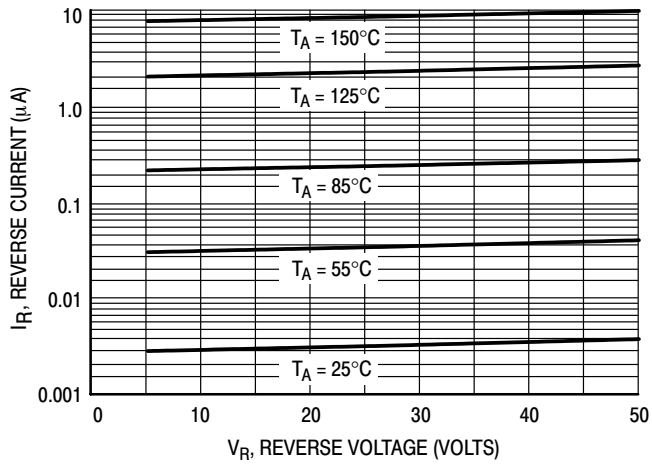


Figure 3. Leakage Current

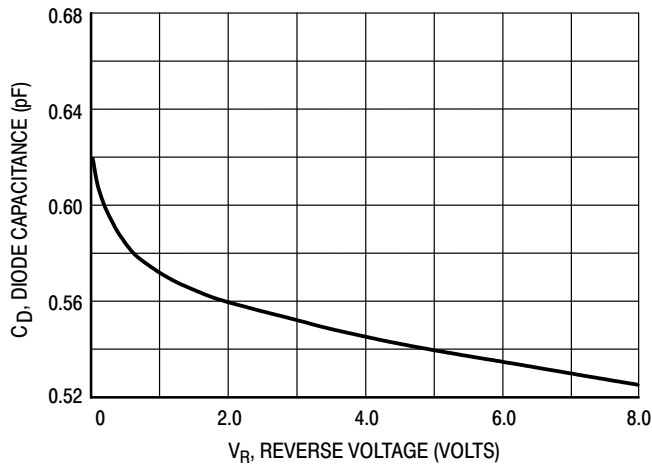


Figure 4. Capacitance

